













Year	event	notes
1947	bipolar transistor	Shockley-Brittain-Bardeen - Bell Labs
1956	Nobel Prize	
1954	bipolar transistor, grown junction technique	Texas Instruments
main d	ifficulties: high purity material and doping technic	que; surface passivation
1957-	diffusion doping technique	
1958		
1961	oxidation of Silicon surface	Germanium abandoned
next ad	vance: integration of several devices	
1959	patent of original idea	Jack Kilby - Texas Instruments
1961	patent of planar technology and microchip	Robert Noyce, co-founder of Fairchild
	integrated circuit	and Intel
		Jean Horni - Fairchild
1961	use of planar technology for discrete	
hinolar	transistors -> MOS transistors	
1060	first reliable MOS transistor	
1962	first MOS IC marketed	
mid-	mastering of all aspects of IC technology	
1960's	indetaining of all depote of to definitions gy	
1965-20	00: unique progress !!!	
	device dimensions: factor 10000	
	integration scale: factor 1000000	

























quantity	unit		description
length	meter	m	length of path traveled by light in vacuum during a time interval of 1/299 792 458 of a second
mass	kilogram	kg	equal to the mass of the international prototype of the kilogram
time	second	S	duration of 9 192 631 770 periods of the radiation corresponding to the transition between the two hyperfine levels of the ground state of the cesium-133 atom
current	ampere	A	that constant current which, if maintained in two straight parallel conductors of infinite length, negligible circular cross section, and placed 1 meter apart in vacuum, would produce a force equal to 2 x 10e7 newtons per meter of length
temperature	kelvin	к	the fraction 1/273.16 of the thermodynamic temperature of the triple point of water
quantity	mole	mol	amount of substance of a system which contains as many elementary units as there are atoms in 0.012 kg of carbon 12 (i.e. Avogardro's number N = 6.022x10e23)
intensity	candela	cd	luminous intensity, in a given direction, of a source that emits monochromatic radiation of frequency 540x10e12 hertz and has a radiant intensity of 1/683 watts/steradian

quantity	unit		description
force	newton	N	(m kg s ⁻ -2) that force which, when applied to a body having a mass of 1 kg, gives it an acceleration of 1 m/s ²
energy	joule	J	(m ² kg s ²) the work done when the point of application of a force is displaced a distance of 1 meter in the direction of the force
power	watt	w	(m ² kg s ⁻³) power corresponding to the production of energy at a rate of 1 joule per second
potential	volt	V	(m ² kg s ³ -3 A ³ -1) difference of electric potential between two points of a conductor carrying a constant current of 1 ampere, when the power dissipated between these points is equal to 1 watt
resistance	ohm	Ω	(m ² kg s ³ 3 A ² 2) electric resistance between two points of a conductor, when a constant differenceof potential of 1 volt, applied between these two points, produces a current of 1 ampere
conductance	siemens	S	conductance = 1 / resistance
capacitance	farad	F	(m ² kg ² kg ³



Some General Constants		More constant
Avogadro's number	$N_{\rm A} = 6.02 \times 10^{23}$ molecules/mole	significant digit
Boltzmann constant	$k_{\rm B} = 1.38 \times 10^{-23} {\rm J/K}$	see appendice
	$= 8.63 \times 10^{-5} \text{ eV/K}$	textbooks and
Coulomb constant	$1/4\pi\epsilon_{\rm O} = 8.99 \times 10^9 \text{N-m}^2/\text{C}^2$	
Gravitational constant	$G = 6.67 \times 10^{-11} \text{ N-m}^2/\text{kg}^2$	
Permittivity of free space	$\epsilon_{\rm O}$ = 8.85 × 10 ⁻¹² C ² /N-m ²	L.Anderson, ed.
Planck constant	$h = 6.63 \times 10^{-34}$ J-sec	A Physicist's
	$= 4.14 \times 10^{-15} \text{ eV-sec}$	Desk Reference
Speed of light	$c = 3.00 \times 10^8 \mathrm{m/sec}$	AIP, New York
Universal gas constant	R = 8.31 J/mole-K	
$1 \text{ eV} = 1.6022 \times 10^{-19} \text{ J}$ $1 \text{ fermi} = 10^{-15} \text{ m}$ 1 inch = 2.54 cm	$kT \approx 1/40 \text{ eV}$ at room temperatu 1 gauss = 10^{-4} T 1 atomic mass unit $u = 1.661 \times$ energy equivalent of $1 u (= uc^2)$	ure (293K) 10 ⁻²⁷ kg = 931.5 MeV

Electronic charge	$1.6 \times 10^{-19} \text{ C}$
Mass of the electron	$9.11 \times 10^{-31} \text{ kg}$
Mass of the proton	$1.67 \times 10^{-27} \text{ kg}$
Mass of the neutron	$1.67 \times 10^{-27} \text{ kg}$
Bohr radius	$5.3 \times 10^{-11} \mathrm{m}$
Ionization energy of hydrogen	13.6 eV
Effective mass of electrons in silicon	$0.31 imes 9.11 imes 10^{-31} m kg$
Effective mass of holes in silicon	$0.38 imes 9.11 imes 10^{-31}$ kg
Energy gap (E_g) in silicon	1.1 eV
Effective mass of electrons in germanium	$0.12 \times 9.11 \times 10^{-31}$ kg
Effective mass of holes in germanium	$0.23 \times 9.11 \times 10^{-31}$ kg
Energy gap (E_g) in germanium	0.67 eV

system	atom	nucleus	neutrons and protons
components	nucleus and electrons	neutrons and protons	quarks
typical length	1Á = 10 ⁻¹⁰ m	10 fm = 10 ⁻¹⁴ m	1 fm = 10 ⁻¹⁵ m
typical energy	1 eV ÷ 1keV	1 MeV = 10 ⁶ eV	1 GeV = 10 ⁹ eV
interaction			
MATTER		Strong	Strong
MATTER		strong	strong DTON QUARK







